

Abstract

The present invention provides a method for manufacturing a compound semiconductor substrate. The method for manufacturing a compound semiconductor substrate comprises the steps of:

5 (a) epitaxially growing a compound semiconductor functional layer 2 on a substrate 1,

(b) bonding a support substrate 3 to the compound semiconductor functional layer 2,

10 (c) polishing the substrate 1 and a part of the compound semiconductor functional layer 2 on the side which is in contact with the substrate 1, to remove them,

(d) bonding a thermally conductive substrate 4 having a thermal conductivity higher than that of the substrate 1 to the exposed

15 surface of the compound semiconductor functional layer 2 which is provided in the step (c) to obtain a multilayer substrate and

(d) separating the support substrate 3 from the multilayer substrate.